

# EPIGAP Optronik GmbH

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## Data Sheet

### LED Chip Infrared

**EOLC-925-11**

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Radiation	Type	Electrodes
Infrared	DDH	P (anode) up

	<p>typ. dimension (<math>\mu\text{m}</math>)</p> <p>typ. thickness <math>150 \pm 25 \mu\text{m}</math></p> <p>anode - gold alloy, thickness <math>1.5 \mu\text{m}</math></p> <p>cathode - gold alloy, thickness <math>0.5 \mu\text{m}</math>, structured, 25% covered</p>
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### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	$V_F$		1.15		V
Forward voltage	$I_F = 100 \text{ mA}$	$V_F$		1.2		V
Forward voltage	$I_F = 350 \text{ mA}$	$V_F$		1.35		V
Reverse voltage	$I_R = 100 \mu\text{A}$	$V_R$	5			V
Radiant power*	$I_F = 20 \text{ mA}$	$\Phi_e$		2		mW
Radiant intensity*	$I_F = 100 \text{ mA}$	$I_e$		3.05		mW/sr
Radiant intensity*	$I_F = 350 \text{ mA}$	$I_e$		6.8		mW/sr
Radiant power*	$I_F = 350 \text{ mA}$	$\Phi_e$		24		mW
Peak wavelength	$I_F = 20 \text{ mA}$	$\lambda_p$	915	925	935	nm
FWHM	$I_F = 20 \text{ mA}$	$\Delta\lambda_{0.5}$		60		nm
Switching time	$I_F = 20 \text{ mA}$	$t_r, t_f$		400		ns

\*Measured on bare chip on TO-18 header

### Packing

Chips on adhesive film with wire bond side up

Art. No. 113 053



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.